

08/20/2004

RELIABILITY REPORT FOR

# DS1844, Rev A2

# **Dallas Semiconductor**

4401 South Beltwood Parkway Dallas, TX 75244-3292

Prepared by:

Ken Wendel

Ken Wendel Reliability Engineering Manager Dallas Semiconductor 4401 South Beltwood Pkwy. Dallas, TX 75244-3292 Email : ken.wendel@dalsemi.com ph: 972-371-3726 fax: 972-371-6016 mbl: 214-435-6610

#### **Conclusion:**

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products and processes:

```
DS1844, Rev A2
```

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

### **Device Description:**

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l\_datasheet3.cfm.

### **Reliability Derating:**

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)\*(1/Tu - 1/Ts)) = tu/ts AfT = Acceleration factor due to Temperature tu = Time at use temperature (e.g. 55°C) ts = Time at stress temperature (e.g. 125°C) k = Boltzmann's Constant (8.617 x 10-5 eV/°K) Tu = Temperature at Use (°K) Ts = Temperature at Stress (°K) Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B\*(Vs - Vu)) AfV = Acceleration factor due to Voltage Vs = Stress Voltage (e.g. 7.0 volts) Vu = Maximum Operating Voltage (e.g. 5.5 volts) B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts \* AfV \* AfT \* N \* 2)X = Chi-Sq statistical upper limit N = Life test sample size Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE:	MTTF (YRS): 49791	FITS: 2.3
---------------	-------------------	-----------

The parameters used to calculate this failure rate are as follows:

Cf: 60%	Ea: 0.7	B: 0	Tu: 25 °C	Vu: 5.5 Volts
---------	---------	------	-----------	---------------

The reliability data follows. A the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data.

#### **Device Information:**

Process: Passivation:	1P, 2M, 0.8um, PdplDiode, Low Vts , N+ESD II, WJ BPS Passivation w/Nov TEOS Oxide-Nitride
Die Size:	76 x 92
Number of Transistors:	0
Interconnect:	Aluminum / 1% Silicon / 0.5% Copper
Gate Oxide Thickness:	175 Å

#### ELECTRICAL CHARACTERIZATION

DESCRIPTION	DATE CODE CONDITION		REA	DPOINT	QTY	FAILS	FA#
ESD SENSITIVITY	9820	EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	1	0	
ESD SENSITIVITY	9820	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	2	0	
ESD SENSITIVITY	9820	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	1	0	
ESD SENSITIVITY	9820	EOS/ESD S5.1 HBM 2500 VOLTS	1	PUL'S	3	3	No FA
ESD SENSITIVITY	9820	EOS/ESD S5.1 HBM 3000 VOLTS	1	PUL'S	2	2	No FA
LATCH-UP	9820	JESD78, I-TEST 125C	2	DYS	9	0	
LATCH-UP	9820	JESD78, Vsupply TEST 125C	2	DYS	9	0	
				Total:		5	

OPERATING LIFE

DESCRIPTION	DATE CODE CONDITION		READPOINT		QTY	FAILS	FA#
INFANT LIFE	9525	125C, 7.0 VOLTS	48	HRS	307	0	
HIGH VOLTAGE LIFE	9525	125C, 7.0 VOLTS	1000	HRS	153	0	
HIGH VOLTAGE LIFE	9820	125C, 7.0 VOLTS	1000	HRS	256	0	
				Total:		0	

## TEMPERATURE CYCLE

DESCRIPTION	DATE CO	DDE CONDITION	READPOINT	<b>QTY</b> Β	FAILS	FA#
TEMP CYCLE	9525	-55C TO 125C	1000 CYS	77	0	
			Total:		0	

## TEMPERATURE HUMIDITY BIAS

DESCRIPTION	DATE CODE CONDITION			READPOINT			QTY FAILS		
BIASED MOISTURE	9525	85/85, 5.5 VOLTS		959	HRS	77	0		
					Total:		0		
FAILURE RATE:		MTTF (YRS): 49791	FITS:	2.3					